



### Features

- 40V Darlington Transistor
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- High Current Gain
- Ultra-Small Surface Mount Package
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)

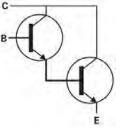
# NPN SURFACE MOUNT DARLINGTON TRANSISTOR

### **Mechanical Data**

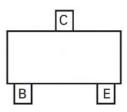
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Weight: 0.006 grams (approximate)



Top View







Pin-out Top view

### Ordering Information (Note 3)

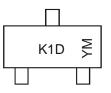
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMST6427-7-F	K1D	7	8	3,000

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

3. For Packaging Details, go to our website at http://www.diodes.com.

### **Marking Information**



K1D= Product Type Marking Code YM = Date Code Marking Y = Year ex: X = 2010 M = Month ex: 9 = September

#### Date Code Key

Year	20	10	20	11	20	12	20	13	20	14	20	15
Code	>	<	٢	(	Z	2	ŀ	4	E	3	(	)
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Νον	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	12	V
Collector Current - Continuous (Note 4)	Ι <sub>C</sub>	500	mA
Power Dissipation (Note 4)	Pd	200	mW
Thermal Resistance, Junction to Ambient (Note 4)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

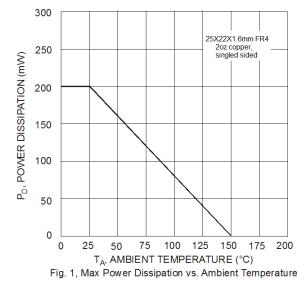
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

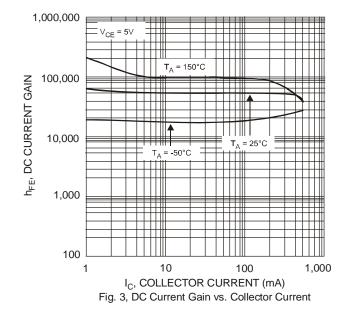
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					·
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40	_	V	$I_{C} = 100 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40	_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	12	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	50	nA	$V_{CB} = 30V, I_E = 0$
Collector Cutoff Current	I <sub>CEO</sub>	_	1.0	μA	$V_{CE} = 25V, I_B = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_	50	nA	$V_{EB} = 10V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h <sub>FE</sub>	10,000 20,000 14,000	100,000 200,000 140,000	_	$I_{C} = 10mA, V_{CE} = 5.0V$ $I_{C} = 100mA, V_{CE} = 5.0V$ $I_{C} = 500mA, V_{CE} = 5.0V$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	1.2 1.5	V	$I_{C} = 50$ mA, $I_{B} = 0.5$ mA $I_{C} = 500$ mA, $I_{B} = 0.5$ mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	2.0	V	$I_{\rm C} = 500$ mA, $I_{\rm B} = 0.5$ mA
Base-Emitter On Voltage	V <sub>BE(on)</sub>	_	1.75	V	I <sub>C</sub> = 50mA, V <sub>CE</sub> =5.0V
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	8.0 T	8.0 Typical		$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Input Capacitance	C <sub>ibo</sub>	15 Typical		pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0

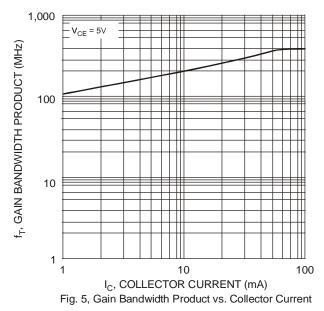
Notes: 4. Device mounted on 25mm x 22 mm x 1.6mm FR4 PCB, 1oz copper, singled sided 5. Short duration pulse test used to minimize self-heating effect.

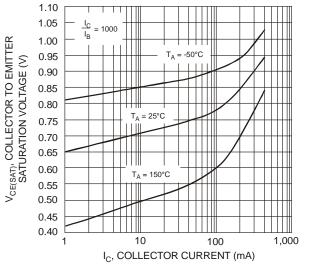


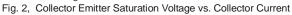
## **MMST6427**

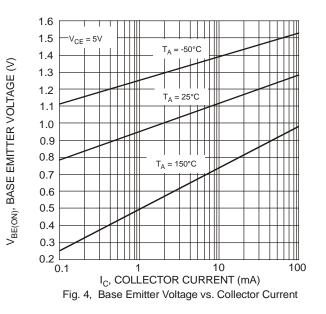








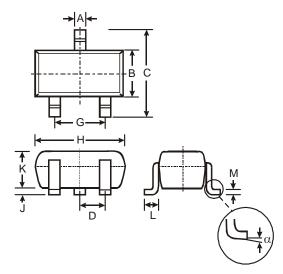




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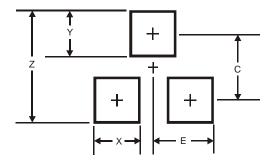


# Package Outline Dimensions



SOT323							
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	-	-	0.65				
G	1.20	1.40	1.30				
н	1.80	2.20	2.15				
<b>ر</b>	0.0	0.10	0.05				
κ	0.90	1.00	1.00				
L	0.25	0.40	0.30				
М	0.10	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0



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